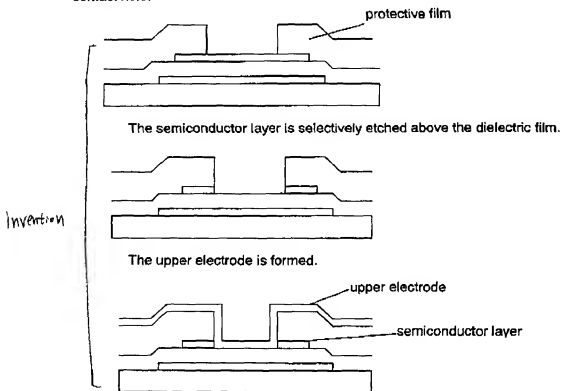
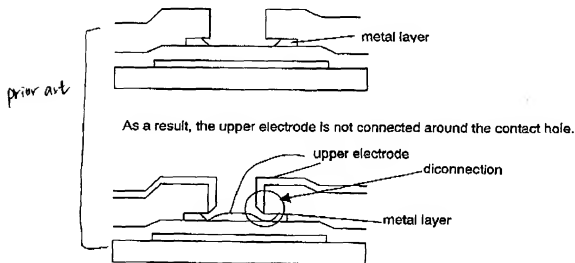


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By using a buffer solution of hydrofluoric acid, the protective film is opened to form the contact hole.



If the metal layer is formed on the dielectric film instead of semiconductor layer, the side edge of the metal layer is scooped out.



Accordingly, it is important that the semiconductor layer forms in the part of surroundings of a contact hole in this invention.